



Bipolar NPN Bare Die – BTN900

Part Description

The BTN900 is a silicon BJT transistor available in bare die form and well suited for use in High Speed Switching applications.

Key Parameters:

- VCBO = 75V
- VCEO = 40V
- VEBO = 6V
- hFE = 100-300 @ VCE = 10V, IC = 0.15A
- VCE(Sat) = 1V @ IC = 0.5A, IB = 50mA
- fT = 300 MHz @ VCE = 20V, IE = 0A
- COBO = 8pF @ VCB = 10V

Features

Designed to provide performance equivalent to FAIRCHILD / ON SEMI MMBT2222A, 2N2222A

Die Size (Unsawn)

350µm X 350µm, 14 Mils X 14 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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